DATA SHEET

BIPOLAR ANALOG INTEGRATED CIRCUITS μ PC2757T, μ PC2758T

SILICON MMIC 1st FREQUENCY DOWN-CONVERTER FOR MOBILE COMMUNICATIONS

DESCRIPTION

NEC

The μ PC2757T and μ PC2758T are silicon monolithic integrated circuits designed as 1st down-converters for L band mobile communications. The ICs consist of mixer and local amplifier. The μ PC2757T features low current consumption and the μ PC2758T features improved intermodulation. From these two version, you can chose either IC corresponding to your system design.

The μ PC2757T and μ PC2758T are manufactured using NEC's 20 GHz fr NESATTM III silicon bipolar process. This process uses silicon nitride passivation film and gold electrodes. These materials can protect chip surface from external pollution and prevent corrosion and migration. Thus, these products have excellent performance, uniformity and reliability.

FEATURES

- Wide band operation : fRFin = 0.1 GHz to 2.0 GHz
- High-density surface mounting : 6-pin minimold
- Low voltage operation
 Supply voltage 3.0 V TYP.
- Low power consumption 15 mW: μPC2757T
- Power-save function : μPC2757T, μPC2758T

ORDERING INFORMATION

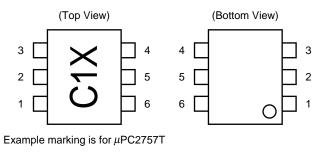
Part Number	Markings	Product Type	Package	Supplying Form
μPC2757T-E3	C1X	Low power consumption	6-pin minimold	Embossed tape 8-mm wide. Pin 1, 2, 3 face to perforation side of the tape.
μPC2758T-E3	C1Y	High output IP₃		QTY 3 kp/Reel.

Note To order evaluation samples, please contact local NEC sales office. (Part number for sample order: μ PC2757T, μ PC2758T)

Caution Electro-static sensitive devices

The information in this document is subject to change without notice. Before using this document, please confirm that this is the latest version. Not all devices/types available in every country. Please check with local NEC representative for availability and additional information.

PIN CONNECTIONS



Pin No.	Pin Name			
1	RF input			
2	GND			
3	LO input			
4	PS			
5	Vcc			
6	IF output			

* PRODUCT LINE-UP (TA = +25 °C, Vcc = 3.0 V, ZL = Zs = 50 Ω)

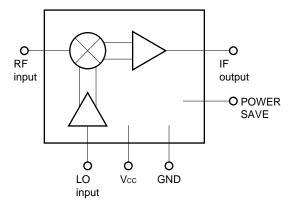
Items Part No.	No RF Icc (mA)	900 MHz SSB NF (dB)	1.5 GHz SSB NF (dB)	1.9 GHz SSB NF (dB)	900 MHz CG (dB)	1.5 GHz CG (dB)	1.9 GHz CG (dB)	900 MHz IIP ₃ (dBm)	1.5 GHz IIP₃ (dBm)	1.9 GHz IIP ₃ (dBm)
μPC2757T	5.6	10	10	13	15	15	13	-14	-14	-12
μPC2757TB	5.0	10	10	15	15	15	15	-14	-14	-12
μPC2758T			10	40	40	40	47	40	40	
μPC2758TB	11	9	10	13	19	18	17	-13	-12	-11
μPC8112T	0.5				45	40	10	10		_
μPC8112TB	8.5	9	11	11	15	13	13	-10	-9	-7

Items Part No.	900 MHz Po _(sat) (dBm)	1.5 GHz Po _(sat) (dBm)	1.9 GHz Po _(sat) (dBm)	900 MHz RF _{lo} (dB)	1.5 GHz RF₀ (dB)	1.9 GHz RFl₀ (dB)	IF Output Configuration	Packages
μPC2757T			0					6-pin minimold
μPC2757TB	-3	_	-8	_	-	-	Emitter follower	6-pin super minimold
μPC2758T			4				Emilier follower	6-pin minimold
μPC2758TB	+1	_	-4	_	-	-		6-pin super minimold
μPC8112T	2.5	-3	-3	80	57	55	Open collector	6-pin minimold
μPC8112TB	-2.5	-3	-3	-80	-57	-55	Open collector	6-pin super minimold

Remark Typical performance. Please refer to ELECTRICAL CHARACTERISTICS in detail. To know the associated product, please refer to each latest data sheet.

Notice μ PC2757 and μ PC2758's IIP₃ are calculated with Δ IM₃ = 3 which is the same IM₃ inclination as μ PC8112. On the other hand, OIP₃ of Standard characteristics in page 4 is cross point IP.

INTERNAL BLOCK DIAGRAM (µPC2757T, µPC2758T IN COMMON)



To know the detail in associated product, please refer to its latest data sheet.

PIN EXPLANATION (BOTH µPC2757T, 2758T)

Pin No.	Pin Name	Applied Voltage (V)	Pin Voltage (V) ^{Note}	Function and Application	Equivalent Circuit
1	RF input	_	1.2	This pin is RF input for mixer designed as double balance type. This circuit contributes to suppress spurious signal with minimum LO and bias power consumption. Also this symmetrical circuit can keep specified performance insensi- tive to process-condition distribution.	From Vcc LO LO To IF Amp.
2	GND	GND	_	This pin is ground of IC. Must be connected to the system ground with minimum inductance. Ground pattern on the board should be formed as wide as possible. (Track length should be kept as short as possible.)	_
3	LO input	_	1.3	This pin is LO input for local buffer designed as differential amplifier. Recommendable input level is –15 to –0 dBm. Also this symmetrical circuit can keep specified performance insensitive to process- condition distribution.	Wixer 3
4	PS	Vcc/GND	-	This pin is for power-save function.This pin can control ON/OFFoperation with bias as follows;Bias: VOperationVPS ≥ 2.5 ON0 to 0.5OFFRise time/fall time using this pin are approximately 10 μ s.	Vcc Vcc
5	Vcc	2.7 to 3.3	_	Supply voltage 3.0 ±0.3 V for operation. Must be connected bypass capacitor. (example: 1 000 pF) to minimize ground impedance.	-
6	IF output	_	1.7	This pin is output from IF buffer amplifier designed as single-ended push-pull type. This pin is assigned for emitter follower output with low- impedance. In the case of connecting to high-impedance stage, please attach external matching circuit.	Vcc 6

Note Each pin voltage is measured with Vcc = 3.0 V

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Conditions	Ratings	Unit
Supply Voltage	Vcc	TA = +25 °C	5.5	V
PS Pin Voltage	Vps	TA = +25 °C	5.5	V
Power Dissipation of Package Allowance	PD	Mounted on $50 \times 50 \times 1.6$ mm double sided copper clad epoxy glass board at T _A = +85 °C	280	mW
Operating Ambient Temperature	TA		-40 to +85	°C
Storage Temperature	Tstg		–55 to +150	°C

RECOMMENDED OPERATING RANGE

Parameters	Symbol	MIN.	TYP.	MAX.	Unit
Supply Voltage	Vcc	2.7	3.0	3.3	V
Operating Ambient Temperature	TA	-40	+25	+85	°C
LO Input Level	PLOin	-15	-10	0	dBm

ELECTRICAL CHARACTERISTICS (TA = +25°C, Vcc = VPs = 3.0 V, PLOin = -10 dBm, ZL = Zs = 50 Ω)

Parameters	Symbol	Conditions	μ	ιPC2757	Т	μ	ιPC2758	Т	Unit
Parameters	Symbol	Conditions	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	Unit
Circuit Current	lcc	No input signal	3.7	5.6	7.7	6.6	11	14.8	dB
RF Frequency Response	f RFin	$CG \ge (CG1 - 3 dB)$ f _{IFout} = 130 MHz constant	0.1		2.0	0.1		2.0	GHz
IF Frequency Response	fiFout	$CG \ge (CG1 - 3 dB)$ f _{RFin} = 0.8 GHz constant	20		300	20		300	MHz
Conversion Gain 1	CG1	$f_{RFin} = 0.8 \text{ GHz}, f_{IFout} = 130 \text{ MHz}$ $P_{RFin} = -40 \text{ dBm}, \text{ Upper local}$	12	15	18	16	19	22	dB
Conversion Gain 2	CG2	$f_{RFin} = 2.0 \text{ GHz}, f_{IFout} = 250 \text{ MHz}$ $P_{RFin} = -40 \text{ dBm}, \text{ Lower local}$	10	13	16	14	17	20	dB
Single Sideband Noise Figure 1	SSB NF1	f _{RFin} = 0.8 GHz, f _{IFout} = 130 MHz, Upper local		10	13		9	12	dB
Single Sideband Noise Figure 2	SSB NF2	f _{RFin} = 2.0 GHz, f _{IFout} = 250 MHz, Lower local		13	16		13	15	dB
Maximum IF Output Level 1	Po(sat) 1	$\label{eq:result} \begin{array}{l} f_{RFin} = 0.8 \; GHz, \\ f_{RFin} = -10 \; dBm, \; Upper \; local \end{array}$	-11	-3		-7	+1		dBm
Maximum IF Output Level 2	Po(sat) 2	$\label{eq:result} \begin{array}{l} f_{\text{RFin}} = 2.0 \text{ GHz}, \\ f_{\text{RFin}} = -10 \text{ dBm}, \\ \text{Lower local} \end{array}$	-11	-8		-7	-4		dBm

STANDARD CHARACTERISTICS FOR REFERENCE

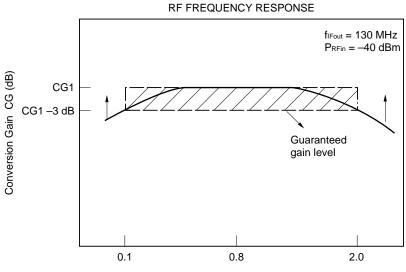
(Unless otherwise specified: $T_A = +25^{\circ}C$, $V_{CC} = V_{PS} = 3.0 \text{ V}$, $P_{LOin} = -10 \text{ dBm}$, $Z_L = Z_S = 50 \Omega$)

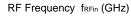
Deremetere	Cumbol	Conditions	Referen	Unit		
Parameters	Symbol Conditions		μPC2757T	μPC2758T	Unit	
Output 3rd intercept point	OIP ₃	$f_{RFin} = 0.8$ to 2.0 GHz, $f_{IFout} = 0.1$ GHz, Cross point IP	+5	+11	dBm	
LO leakage at RF pin	LOrf	fLOin = 0.8 to 2.0 GHz	-35	-30	dBm	
LO leakage at IF pin	LOif	fLoin = 0.8 to 2.0 GHz	-23	-15	dBm	
Power-saving current	IPS	Vps = 0.5 V	0.1	0.1	μA	

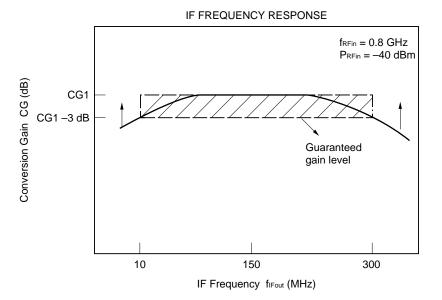
Remark IIP₃ is determined by comparing two method; theoretical calculation and cross point of IM₃ curve. IIP₃ = $(\Delta IM_3 \times P_{in} + CG - IM_3) \div (\Delta IM_3 - 1)$ (dBm) [ΔIM_3 : IM₃ curve inclination in linear range]

SCHEMATIC SUPPLEMENT FOR RF, IF SPECIFICATIONS

	μPC2757T				Unit		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	Unit
CG1	12	15	18	16	19	22	dB
CG1 – 3 dB	9	12	15	13	16	19	dB



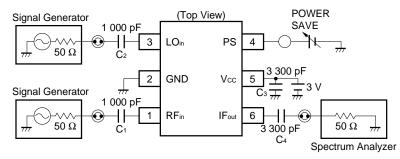




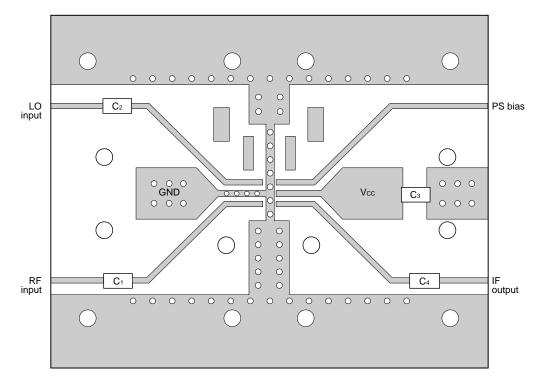
Data Sheet P10716EJ4V0DS00

TEST CIRCUIT

μPC2757T, μPC2758T



★ ILLUSTRATION OF THE TEST CIRCUIT ASSEMBLED ON EVALUATION BOARD



COMPONENT LIST

No.	Value
C1, C2	1 000 pF
C ₃ to C ₅	3 300 pF

- **Notes 1.** $35 \times 42 \times 0.4$ mm double sided copper clad polyimide board.
 - 2. Back side: GND pattern
 - 3. Solder plated on pattern
 - 4. °O: Through holes

APPLICATION

This IC is guaranteed on the test circuit constructed with 50 Ω equipment and transmission line.

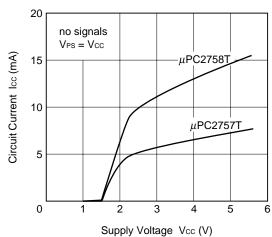
This IC, however, does not have 50 Ω input/output impedance, but electrical characteristics such as conversion gain and intermodulation distortion are described herein on these conditions without impedance matching. So, you should understand that conversion gain and intermodulation distortion at input level will vary when you improve VS of RF input with external circuit (50 Ω termination or impedance matching).

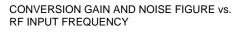
External circuits of the IC can be referred to following application notes.

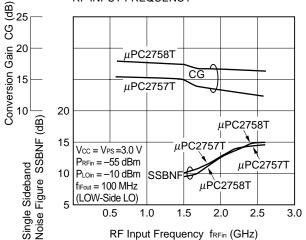
• To RF and IF port: μPC2757, μPC2758, μPC8112 application note (Document No. P11997E)

TYPICAL CHARACTERISTICS ($T_A = +25 °C$)

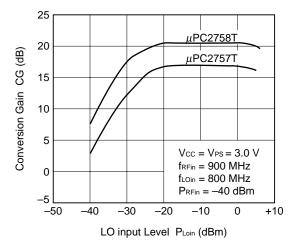
CIRCUIT CURRENT vs. SUPPLY VOLTAGE

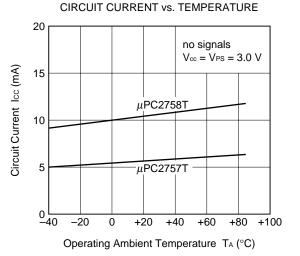




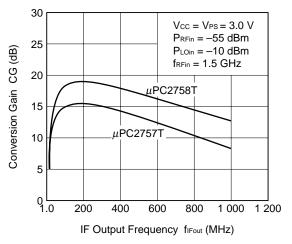


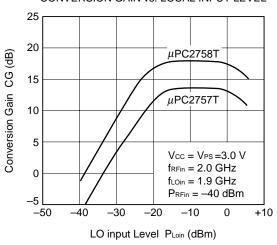
CONVERSION GAIN vs. LOCAL INPUT LEVEL



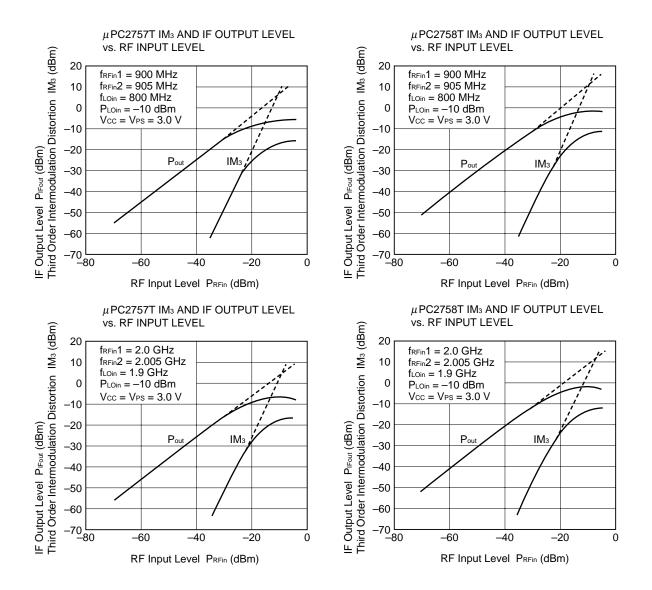


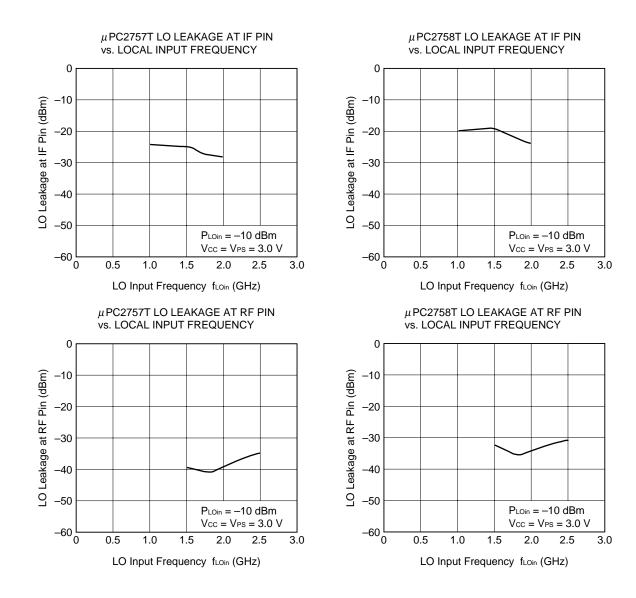
CONVERSION GAIN vs. IF OUTPUT FREQUENCY





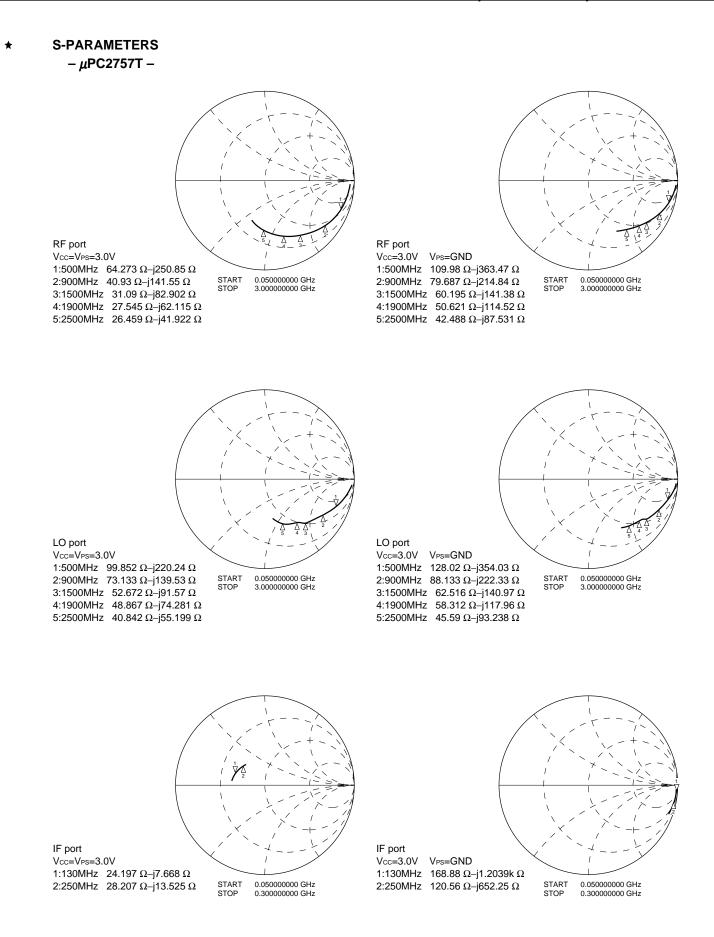
CONVERSION GAIN vs. LOCAL INPUT LEVEL





NEC

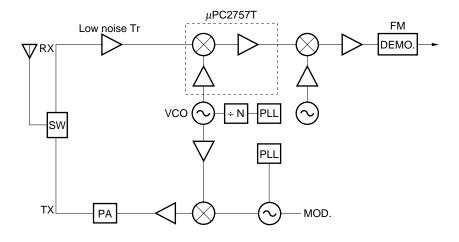
NEC



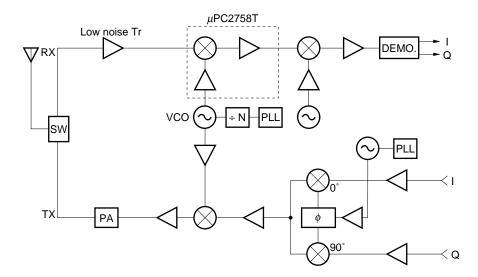
- μPC2758T -RF port RF port Vcc=3.0V Vps=GND Vcc=VPs=3.0V 1:500MHz 59.633 Ω-j235.09 Ω 1:500MHz 105.94 Ω-j355.98 Ω START STOP 0.05000000 GHz 3.00000000 GHz START STOP 0.05000000 GHz 3.00000000 GHz 2:900MHz 37.609 Ω-j131.38 Ω 2:900MHz 79.336 Ω-j214.39 Ω 3:1500MHz 29.121 Ω-j76.48 Ω 3:1500MHz 61.398 Ω-j139.99 Ω 4:1900MHz 26.992 Ω-j56.742 Ω 4:1900MHz 51.539 Ω -j113.45 Ω 5:2500MHz 26.697 Ω-j37.975 Ω 5:2500MHz 42.875 Ω-j87.09 Ω LO port LO port Vcc=Vps=3.0V Vcc=3.0V Vps=GND 1:500MHz 102.48 Ω–j330.11 Ω 1:500MHz 69.883 Ω -j177.5 Ω 0.05000000 GHz 3.00000000 GHz 0.05000000 GHz 3.00000000 GHz START STOP START STOP 2:900MHz 59.047 Ω-j102.83 Ω 2:900MHz 79.703 Ω-j199.25 Ω 3:1500MHz 49.656 Ω -j67.445 Ω 3:1500MHz 60.961 Ω-j128.63 Ω 4:1900MHz 46.871 Ω–j53.65 Ω 4:1900MHz 59.211 Ω-j107.32 Ω 5:2500MHz 42.143 Ω -j40.105 Ω 5:2500MHz 48.105 Ω-j86.215 Ω IF port IF port Vcc=Vps=3.0V Vcc=3.0V Vps=GND 1:130MHz 20.784 Ω -j10.842 Ω 1:130MHz 182.06 Ω -j1.1831k Ω 0.05000000 GHz 0.30000000 GHz START 0.05000000 GHz START 2:250MHz 27.586 Ω-j18.538 Ω 2:250MHz 117.16 Ω-j631.63 Ω STOP 0.300000000 GHz STOP

SYSTEM APPLICATION EXAMPLE

ANALOG CELLULAR TELEPHONE



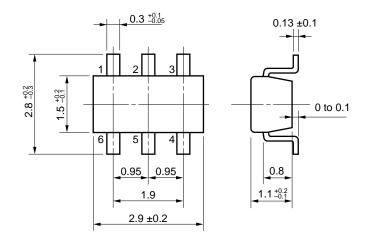
DIGITAL CELLULAR TELEPHONE



These examples show only IC's location on the system use schematically, do not present or recommend the actual application circuit in detail.

PACKAGE DIMENSIONS

6 PIN MINIMOLD (Unit: mm)



NOTE ON CORRECT USE

- (1) Observe precautions for handling because of electrostatic sensitive devices.
- (2) Form a ground pattern as wide as possible to minimize ground impedance (to prevent undesired oscillation).
- (3) Keep the track length of the ground pins as short as possible.
- (4) Connect a bypass capacitor (example: 1 000 pF) to the Vcc pin.

RECOMMENDED SOLDERING CONDITIONS

This product should be soldered under the following recommended conditions. For soldering methods and conditions other than those recommended below, contact your NEC sales representative.

Soldering Method	Soldering Conditions	Recommended Condition Symbol
Infrared Reflow	Package peak temperature: 235 °C or below Time: 30 seconds or less (at 210 °C) Count: 3, Exposure limit: None ^{Note}	IR35-00-3
VPS	Package peak temperature: 215 °C or below Time: 40 seconds or less (at 200 °C) Count: 3, Exposure limit: None ^{Note}	VP15-00-3
Wave Soldering	Soldering bath temperature: 260 °C or below Time: 10 seconds or less Count: 1, Exposure limit: None ^{Note}	WS60-00-1
Partial Heating	Pin temperature: 300 °C Time: 3 seconds or less (per side of device) Exposure limit: None ^{Note}	-

Note After opening the dry pack, keep it in a place below 25 °C and 65 % RH for the allowable storage period.

Caution Do not use different soldering methods together (except for partial heating).

For details of recommended soldering conditions for surface mounting, refer to information document SEMICONDUCTOR DEVICE MOUNTING TECHNOLOGY MANUAL (C10535E).



NESAT (NEC Silicon Advanced Technology) is a trademark of NEC Corporation.

- The information in this document is subject to change without notice. Before using this document, please confirm that this is the latest version.
- No part of this document may be copied or reproduced in any form or by any means without the prior written consent of NEC Corporation. NEC Corporation assumes no responsibility for any errors which may appear in this document.
- NEC Corporation does not assume any liability for infringement of patents, copyrights or other intellectual property
 rights of third parties by or arising from use of a device described herein or any other liability arising from use
 of such device. No license, either express, implied or otherwise, is granted under any patents, copyrights or other
 intellectual property rights of NEC Corporation or others.
- Descriptions of circuits, software, and other related information in this document are provided for illustrative purposes in semiconductor product operation and application examples. The incorporation of these circuits, software, and information in the design of the customer's equipment shall be done under the full responsibility of the customer. NEC Corporation assumes no responsibility for any losses incurred by the customer or third parties arising from the use of these circuits, software, and information.
- While NEC Corporation has been making continuous effort to enhance the reliability of its semiconductor devices, the possibility of defects cannot be eliminated entirely. To minimize risks of damage or injury to persons or property arising from a defect in an NEC semiconductor device, customers must incorporate sufficient safety measures in its design, such as redundancy, fire-containment, and anti-failure features.
- NEC devices are classified into the following three quality grades:
 "Standard", "Special", and "Specific". The Specific quality grade applies only to devices developed based on a
 customer designated "quality assurance program" for a specific application. The recommended applications of
 a device depend on its quality grade, as indicated below. Customers must check the quality grade of each device
 before using it in a particular application.
 - Standard: Computers, office equipment, communications equipment, test and measurement equipment, audio and visual equipment, home electronic appliances, machine tools, personal electronic equipment and industrial robots
 - Special: Transportation equipment (automobiles, trains, ships, etc.), traffic control systems, anti-disaster systems, anti-crime systems, safety equipment and medical equipment (not specifically designed for life support)
 - Specific: Aircraft, aerospace equipment, submersible repeaters, nuclear reactor control systems, life support systems or medical equipment for life support, etc.

The quality grade of NEC devices is "Standard" unless otherwise specified in NEC's Data Sheets or Data Books. If customers intend to use NEC devices for applications other than those specified for Standard quality grade, they should contact an NEC sales representative in advance.

M7 98.8